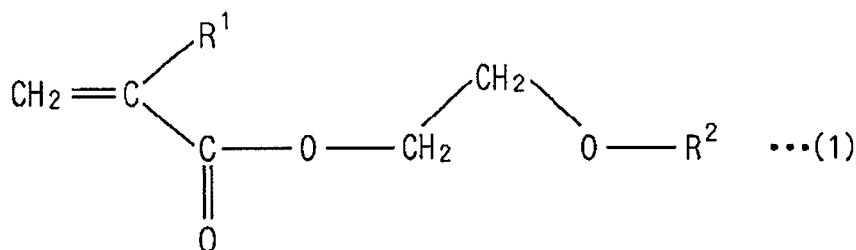


AMENDMENTS TO THE CLAIMS

1. **(Currently amended)** A thick film photoresist composition comprising:

(A) a resin component containing (a) from 61 to 90% by weight of a structural unit derived from a cyclic alkyl (meth)acrylate ester, and (b) a structural unit derived from a radical polymerizable compound containing a hydroxyl group, and (c) a structural unit derived from a radical polymerizable compound represented by a general formula (1) shown below:



(wherein, R¹ represents a hydrogen atom or a methyl group, and R² represents a hydrogen atom or an alkyl group of 1 to 4 carbon atoms).

(B) a polymerizable compound containing at least one ethylenic unsaturated double bond;

(C) a photopolymerization initiator; and

(D) an organic solvent.

2. **(Original)** A thick film photoresist composition according to claim 1, wherein said structural unit (b) accounts for at least 1% by weight, but less than 10% by weight, of said component (A).

3. **(Canceled)**

4. **(Previously presented)** A thick film photoresist composition according to claim 1, wherein said component (D) is methyl isobutyl ketone and/or methyl ethyl ketone.

5. (Original) A method of forming a resist pattern, wherein said resist pattern is formed using a thick film photoresist composition according to any one of claim 1 through claim 4.

6. (Previously presented) A pattern formed using the method according to claim 5.

7. (New) A thick film photoresist composition according to claim 1, wherein said resin component contains 65 to 75 % by weight of said structural unit (a).

8. (New) A thick film photoresist composition according to claim 1, wherein component (c) is 2-methoxyethyl acrylate.

9. (New) A thick film photoresist composition comprising:

(A) a resin component containing (a) 65 to 75 % by weight of a structural unit derived from a cyclic alkyl (meth)acrylate ester, and (b) a structural unit derived from a radical polymerizable compound containing a hydroxyl group,

(B) a polymerizable compound containing at least one ethylenic unsaturated double bond,

(C) a photopolymerization initiator, and

(D) an organic solvent.

10. (New) A thick film photoresist composition according to claim 9, wherein said structural unit (b) accounts for at least 1% by weight, but less than 10% by weight, of said component (A).

11. (New) A thick film photoresist composition according to claim 9, wherein said component (D) is methyl isobutyl ketone and/or methyl ethyl ketone.

12. (New) A method of forming a resist pattern, wherein said resist pattern is formed using a thick film photoresist composition according to any one of claim 9 through claim 11.